

# MOS FIELD EFFECT TRANSISTOR 2SJ559

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR HIGH SPEED SWITCHING

#### **DESCRIPTION**

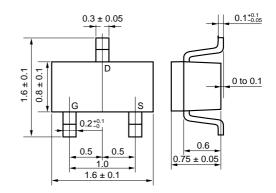
The 2SJ559 is a switching device which can be driven directly by a 2.5 V power source.

The 2SJ559 has excellent switching characteristics, and is suitable for use as a high-speed switching device in digital circuits.

#### **FEATURES**

- Can be driven by a 2.5 V power source.
- · Low gate cut-off voltage.

# PACKAGE DRAWING (Unit: mm)



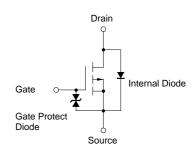
# ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	Vgss	∓ 20	V
Drain Current (DC)	I <sub>D(DC)</sub>	∓ 0.1	Α
Drain Current (pulse) Note1	ID(pulse)	∓ 0.4	Α
Total Power Dissipation Note2	P⊤	200	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1 %

2. Mounted on ceramic substrate of  $3.0 \text{cm}^2 \times 0.64 \text{ mm}$ 

#### **EQUIVALENT CIRCUIT**



Marking: C1

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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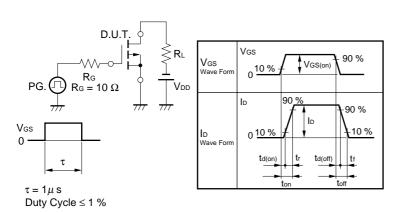
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



# ELECTRICAL CHARACTERISTICS (TA = 25 °C)

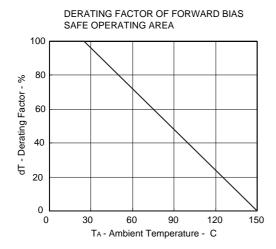
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	Vps = -30 V, Vgs = 0 V			-1	μΑ
Gate Leakage Current	lgss	$V_{GS} = \mp 20 \text{V},  V_{DS} = 0 \text{V}$			∓10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -10 \mu\text{A}$	-1.0	-1.4	-1.7	٧
Forward Transfer Admittance	yfs	$V_{DS} = -3 \text{ V}, I_{D} = -10 \text{ mA}$	20			mS
Drain to Source On-state Resistance	RDS(on)1	Vgs = -2.5 V, Ib = -1 mA		23	60	Ω
	RDS(on)2	$V_{GS} = -4 \text{ V}, I_{D} = -10 \text{ mA}$		11	23	Ω
	RDS(on)3	$V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ mA}$		6	13	Ω
Input Capacitance	Ciss	Vps = -3 V		5		pF
Output Capacitance	Coss	V <sub>G</sub> S = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		1.3		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = -3 V		140		ns
Rise Time	tr	I <sub>D</sub> = -10 mA		330		ns
Turn-off Delay Time	td(off)	$V_{GS(on)} = -4 V$		220		ns
Fall Time	tf	$R_G = 10 \Omega$ , $R_L = 300 \Omega$		320		ns

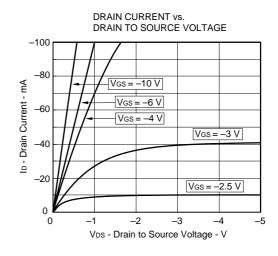
### **TEST CIRCUIT SWITCHING TIME**

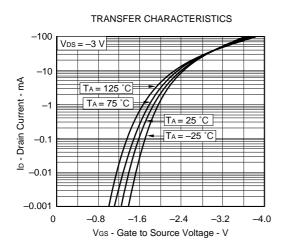


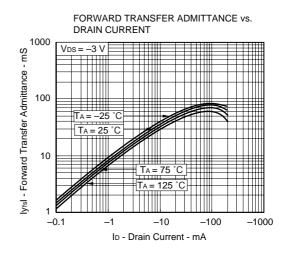


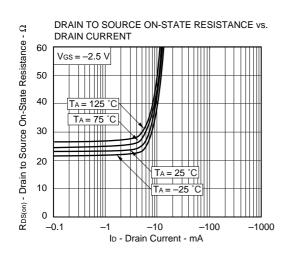
#### TYPICAL CHARACTERISTICS (TA = 25°C)

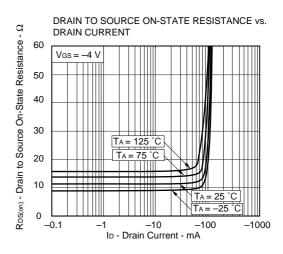




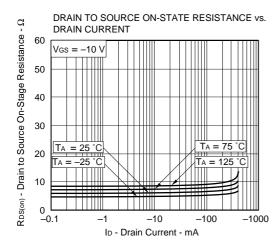


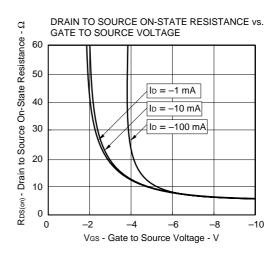


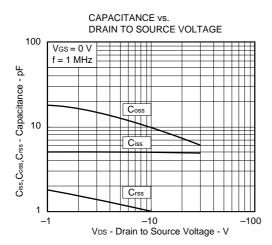


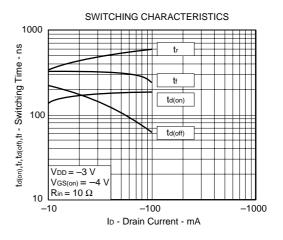


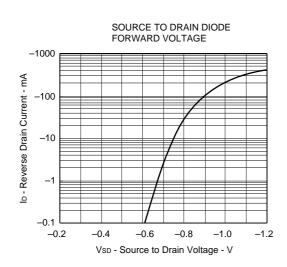
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